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an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough a plurality of wiring grooves which each reaches part of an associated nitride film pattern including said hole patterns; and

wiring metal that fills said first holes, and said wiring grooves;

and wherein said nitride film patterns are separate from each other and a shape and size that extends from the outside of their associated wiring groove.

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3. (Twice Amended) A semiconductor device, comprising:
an underlayer;
a base oxide film with first holes formed on the underlayer;
a plurality of nitride film patterns on the base oxide film, the nitride film patterns having formed therethrough hole patterns, respectively, which are formed directly connected to and wider than said first holes respectively;

an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough a plurality of wiring grooves which each exposes part of the nitride film patterns including said hole patterns; and

wiring metal that fills part of each of the exposed nitride film patterns, each of said first said holes, each of said hole patterns, and each of said wiring grooves;

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and wherein an outer shape of each of said nitride film patterns is substantially the same as the shape of the opening of each of said wiring grooves, an internal wall surface of each of said wiring grooves is tapered from the opening on an upper surface of said upper oxide film to upper surface of each of said nitride film patterns, and neighbouring nitride film patterns are separate from each other.

4. (Twice Amended) A semiconductor device, comprising:

an underlayer;
a base oxide film formed on the underlayer, the base oxide film having formed therethrough a plurality of first holes;
an upper oxide film provided on the base oxide film, the upper oxide film having formed therethrough wiring grooves which are connected to said first holes, respectively; and
barrier and wiring metal that fills each of said first holes and each of said wiring grooves, said barrier and wiring metal having a first portions on the base oxide film and second portions at a middle section of said upper oxide film above said first portions, and each of said first portions having a width W1 smaller than a width W3 of each of the second portions.